

**Amendments to the Specification:**

Please replace paragraph [0033] with the following amended paragraph:

**[0033]**        **Fig. 1** shows a cut-away portion of a semiconductor wafer processing apparatus 10, for example, an ionized physical vapor deposition (iPVD) apparatus as described in U.S. Patents Nos. 6,080,287 or 6,287,435, or an etching apparatus as described in U.S. Patent Application Serial No. ~~09/875,339~~ No. 6,652,711, each hereby expressly incorporated herein by reference. **Fig. 1A** is a perspective diagram of an embodiment of an apparatus 10 of **Fig. 1**. Such an apparatus 10 includes a vacuum processing chamber 12 in which is supported a semiconductor wafer or other substrate 14 for processing. The apparatus 10 includes a chamber wall either formed of a dielectric material, such as alumina or quartz for example, or having a dielectric window 16 formed therein. Behind the dielectric window 16, outside of the chamber, is provided an RF energy source (not shown in its entirety) having an inductive element or antenna 20, coupled to an RF generator 18 through a matching network 17. The generator 18 commonly operates at the industrial frequency of 13.56 MHz to supply energy through the antenna 20 from which it is inductively coupled into the chamber 12 to form a high density plasma 15 therein for processing the substrate 12.